

THE STRUCTURE PROPERTIES
OF IMPLANTED LAYERS OF ARSENIDE
GALLIUM IN ELASTIC DEFORMATION FIELDS

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S u m m a r y

By the method of double-crystal X-ray diffractometry, we have studied the influence of mechanical stresses caused by ion implantation and by grinding one of the surfaces of crystals GaAs on the redistribution of point defects in the near-surface region. The nonmonotone character of a relaxation of deformations in the system 'implanted layer - matrix - polish layer', which consists in different displacement speeds of point defects in the fields of elastic deformations, is explained.